

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

Please amend claims 1, 3, 4, 8, 11, 15, 19 and 21-24 as follows:

1. (Amended) A method for joining a semiconductor die to a leadframe comprising the steps of:

providing a semiconductor die and a leadframe;

forming at least three pedestals raised above a surface of said leadframe in a mounting area adapted for receiving said semiconductor die attached thereto, each of said pedestals having substantially the same pedestal height;

introducing [an adhesive material] solder onto said mounting area[~~, said adhesive material including~~];

heating to urge said solder to deform and to include an average thickness being at least as great as said pedestal height; and

joining said semiconductor die to said mounting area and urging said solder to solidify such that said semiconductor die contacts each of said pedestals and said [adhesive material] solder.

3. (Amended) The method as in claim 1, in which said [adhesive material] solder comprises [an epoxy] a tin/lead eutectic.

4. (Amended) The method as in claim 1, in which said [adhesive material] solder comprises a [~~thermally curable epoxy and said step of joining includes heating to cure said epoxy~~] silver alloy.

8. (Amended) The method as in claim 1, in which said step of providing includes providing said semiconductor die having a top including a semiconductor device formed thereon, sides, and a bottom for contacting said pedestals, and in which said step of introducing includes introducing [a deformable adhesive material to a sufficient thickness] sufficient solder such that said [step of] heating and joining urges portions of said [adhesive material] solder to extend at least partially along said sides of said semiconductor die when said bottom contacts said pedestals.

11. (Amended) An assembly comprising a semiconductor die attached to a surface of a leadframe by [an adhesive] solder, said leadframe including at least three pedestals one of protruding from and formed over said surface, each of said pedestals having substantially the same pedestal height, and said semiconductor die contacting each of said pedestals.

15. (Amended) The assembly as in claim 11, in which said [semiconductor die includes an area which lies within the range of 256 mils<sup>2</sup> to 1 inch<sup>2</sup>] solder comprises a tin/lead eutectic.

19. (Amended) The assembly as in claim 11, wherein said [adhesive] solder comprises [an epoxy] a silver alloy.

21. (Amended) The assembly as in claim 11, in which said semiconductor die includes an integrated circuit formed thereon, an opposed bottom surface contacting said [adhesive] solder and said pedestals and facing said leadframe, and sides, and said [adhesive] solder extends at least partially up said sides.

22. (Amended) The assembly as in claim 11, in which said [adhesive] solder laterally surrounds each of said pedestals and is interposed between said semiconductor die and said surface, has a thickness substantially equal to said pedestal height, and therefore contacts [and adheres to each of] said semiconductor die and said leadframe.

23. (Amended) The assembly as in claim 22, in which said semiconductor die includes a top surface including circuitry thereon, an opposed bottom surface contacting said [adhesive] solder and said pedestals and facing said leadframe, and sides, and said [adhesive] solder extends at least partially up said sides.

24. (Amended) The assembly as in claim 22, in which said [adhesive] solder is characterized as being void-free between said semiconductor die and said surface.